

## REMARKS/ARGUMENTS

Applicant responds herein to the Office Action dated April 11, 2006. A Petition for Extension of Time (one month) and the fee therefor are enclosed.

Claims 1-17, 19-35, and 37 were rejected under 35 U.S.C. §102(b) as being anticipated by Matsuyama et al., JP 2000-340559. Reconsideration of the rejection is respectfully requested.

Independent claim 1 provides, in pertinent part, for, “[a] method for manufacturing a semiconductor device, comprising a dual-stage deposition step comprising ... wherein said metal oxide film as an oxide of said specified metal is formed on said semiconductor substrate, by repeating said dual-stage deposition step two or more times.” Independent claim 19 provides, in pertinent part, for, “[a] method for manufacturing a semiconductor device having a capacitor, comprising: a dual-stage deposition step ... wherein said metal oxide film as an oxide of said specified metal is formed on said semiconductor substrate, by repeating said dual-stage deposition step two or more times ...” Independent claim 37 provides for, “[a] method for manufacturing a semiconductor device, comprising the steps of: a first stage for introducing a material gas containing an oxide of a desired metal into a reaction chamber in which a semiconductor substrate on a right side of which a metal film is formed is placed to thus form an oxide film made of said desired metal by a vapor-phase growth method and, after completion of the first stage, a following second stage for removing from said reaction chamber said material gas introduced into said reaction chamber at said first stage and a byproduct produced at said first stage and, after completion of the second stage, then introducing said material gas continuously for a lapse of time longer than said first stage, thereby forming an oxide film made of said metal having a finally required film thickness.”

In contrast, Matsuyama et al. nowhere discloses, teaches, or suggests repeating the dual-stage deposition step specified in independent claims 1 and 19 two or more times. Likewise, Matsuyama et al. does not teach, disclose, or suggest “introducing said material gas continuously for a lapse of time longer than said first stage,” as specified in independent claim 37.

Since each of claims 2-17 and 20-35 is directly or indirectly dependent upon one of independent claims 1 and 19, each of claims 2-17 and 20-35 is allowable over Matsuyama et al.

for the same reasons recited above with respect to the allowability of independent claims 1 and 19 over Matsuyama et al.

Claims 18 and 36 were rejected under 35 U.S.C. §103(a) as being unpatentable over Matsuyama et al. in view of Roberts et al., U.S. Patent No. 6,461,914 B2. Reconsideration of the rejection is respectfully requested.

Since claim 18 is indirectly dependent upon independent claim 1, and since claim 36 is indirectly dependent upon independent claim 19, each of claims 18 and 36 is allowable over Matsuyama et al. for the same reasons recited above with respect to the allowability of independent claims 1 and 19 over Matsuyama et al. With regard to Roberts et al., the features of independent claims 1, 19, and 37 specified above with respect to the allowability of those claims over Matsuyama et al. are likewise not disclosed, taught, or suggested by Roberts et al.

In view of the foregoing remarks, allowance of claims 1-37 is respectfully requested.

Accordingly, the Examiner is respectfully requested to reconsider the application, allow the claims and pass this case to issue.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Mail Stop AF, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on July 13, 2006:

Max Moskowitz

Name of applicant, assignee or  
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Signature

July 13, 2006

Date of Signature

Respectfully submitted,

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